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Physical characterization of hafnium aluminates dielectrics deposited by atomic layer deposition
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FOREWORD

This year is specially challenging to JICS in its path to increase visibility and attraction of high quality papers. As decided last year, instead of publishing two issues, as is being done since the beginning, we will move to a publication of three issues in the year.

Also the papers included in each issue will not be separated by their main fields, associated with the two main conferences in the field held in Brazil, the Symposium on Microelectronics Technology and Devices – SBMicro – and the Symposium on Integrated Circuits and Systems Design – SBCCI.

In this issue one can find some of the papers that have been selected from those presented at SBMicro2014 (29th Symposium on Microelectronics Technology and Devices), which has been held in Aracaju, Brazil, in 2014. Among the contributions presented at the Symposium, only a few best rated were selected by the JICS Editorial Board and have been invited to submit an extended version to the Journal. These extended papers have passed through the usual reviewing process before acceptance.

In addition to the best papers presented at the conference, spontaneous submissions passed through the usual reviewing process and have been accepted as regular papers.

We would like to thank the authors for their effort in preparing these high quality papers, as well as the reviewers for their valuable contribution on paper evaluation and selection, which guarantees the scientific level of this issue. We sincerely hope that JICS readers will enjoy these contributions.

Marcelo Antonio Pavanello
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